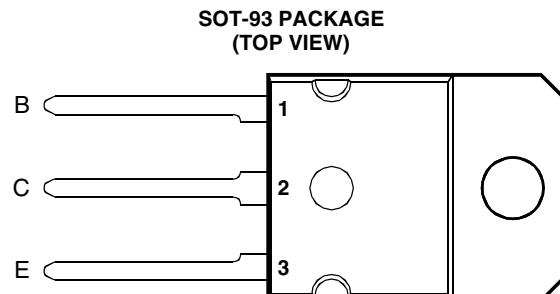


- Designed for Complementary Use with BDW84, BDW84A, BDW84B, BDW84C and BDW84D
- 150 W at 25°C Case Temperature
- 15 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3V, 6 A



Pin 2 is in electrical contact with the mounting base.

MDTRAAA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Collector-base voltage ($I_E = 0$)	BDW83	V_{CBO}	45	V
	BDW83A		60	
	BDW83B		80	
	BDW83C		100	
	BDW83D		120	
Collector-emitter voltage ($I_B = 0$) (see Note 1)	BDW83	V_{CEO}	45	V
	BDW83A		60	
	BDW83B		80	
	BDW83C		100	
	BDW83D		120	
Emitter-base voltage	V_{EBO}		5	V
Continuous collector current	I_C		15	A
Continuous base current	I_B		0.5	A
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)	P_{tot}		150	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)	P_{tot}		3.5	W
Unclamped inductive load energy (see Note 4)	$\frac{1}{2}LI_C^2$		100	mJ
Operating junction temperature range	T_j		-65 to +150	°C
Operating temperature range	T_{stg}		-65 to +150	°C
Operating free-air temperature range	T_A		-65 to +150	°C

NOTES: 1. These values apply when the base-emitter diode is open circuited.

2. Derate linearly to 150°C case temperature at the rate of 1.2 W/°C.

3. Derate linearly to 150°C free air temperature at the rate of 28 mW/°C.

4. This rating is based on the capability of the transistor to operate safely in a circuit of: $L = 20 \text{ mH}$, $I_{B(on)} = 5 \text{ mA}$, $R_{BE} = 100 \Omega$, $V_{BE(off)} = 0$, $R_S = 0.1 \Omega$, $V_{CC} = 20 \text{ V}$.

PRODUCT INFORMATION

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT	
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = 30 \text{ mA}$	$I_B = 0$	(see Note 5)	BDW83 BDW83A BDW83B BDW83C BDW83D	45 60 80 100 120		V
I_{CEO}	Collector-emitter cut-off current	$V_{CE} = 30 \text{ V}$	$I_B = 0$		BDW83		1	
		$V_{CE} = 30 \text{ V}$	$I_B = 0$		BDW83A		1	
		$V_{CE} = 40 \text{ V}$	$I_B = 0$		BDW83B		1	
		$V_{CE} = 50 \text{ V}$	$I_B = 0$		BDW83C		1	
		$V_{CE} = 60 \text{ V}$	$I_B = 0$		BDW83D		1	
I_{CBO}	Collector cut-off current	$V_{CB} = 45 \text{ V}$	$I_E = 0$		BDW83		0.5	
		$V_{CB} = 60 \text{ V}$	$I_E = 0$		BDW83A		0.5	
		$V_{CB} = 80 \text{ V}$	$I_E = 0$		BDW83B		0.5	
		$V_{CB} = 100 \text{ V}$	$I_E = 0$		BDW83C		0.5	
		$V_{CB} = 120 \text{ V}$	$I_E = 0$		BDW83D		0.5	
		$V_{CB} = 45 \text{ V}$	$I_E = 0$	$T_C = 150^\circ\text{C}$	BDW83		5	
		$V_{CB} = 60 \text{ V}$	$I_E = 0$	$T_C = 150^\circ\text{C}$	BDW83A		5	
		$V_{CB} = 80 \text{ V}$	$I_E = 0$	$T_C = 150^\circ\text{C}$	BDW83B		5	
		$V_{CB} = 100 \text{ V}$	$I_E = 0$	$T_C = 150^\circ\text{C}$	BDW83C		5	
		$V_{CB} = 120 \text{ V}$	$I_E = 0$	$T_C = 150^\circ\text{C}$	BDW83D		5	
I_{EBO}	Emitter cut-off current	$V_{EB} = 5 \text{ V}$	$I_C = 0$				2	mA
h_{FE}	Forward current transfer ratio	$V_{CE} = 3 \text{ V}$	$I_C = 6 \text{ A}$	(see Notes 5 and 6)	750		20000	
		$V_{CE} = 3 \text{ V}$	$I_C = 15 \text{ A}$		100			
$V_{BE(on)}$	Base-emitter voltage	$V_{CE} = 3 \text{ V}$	$I_C = 6 \text{ A}$	(see Notes 5 and 6)			2.5	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_B = 12 \text{ mA}$	$I_C = 6 \text{ A}$	(see Notes 5 and 6)			2.5	V
		$I_B = 150 \text{ mA}$	$I_C = 15 \text{ A}$				4	
V_{EC}	Parallel diode forward voltage	$I_E = 15 \text{ A}$	$I_B = 0$				3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_p = 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$			0.83	°C/W
$R_{\theta JA}$			35.7	°C/W

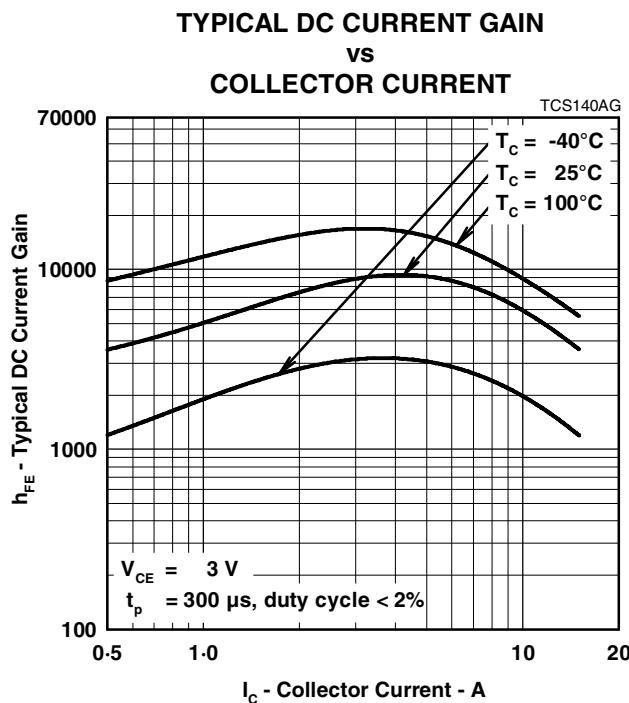
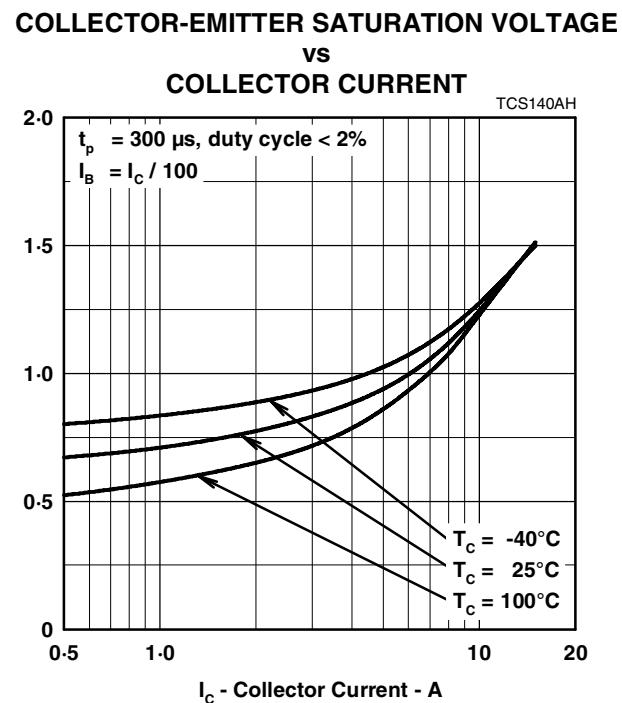
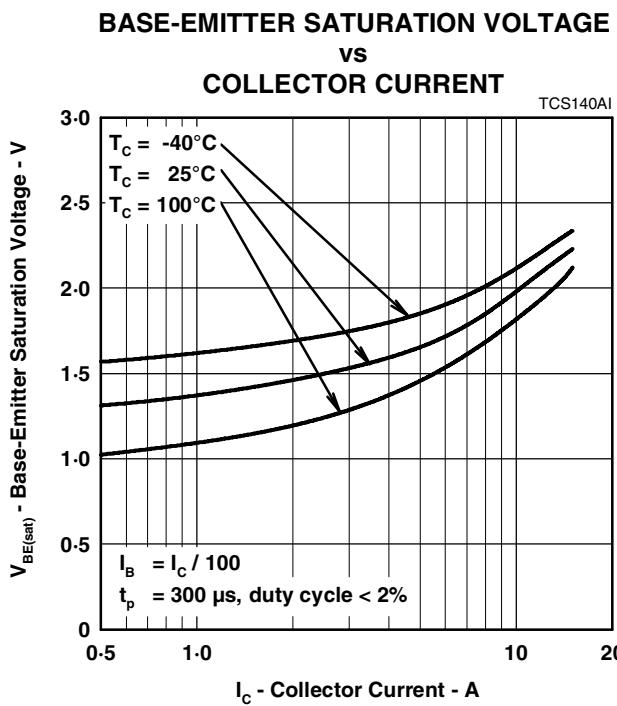
resistive-load-switching characteristics at 25°C case temperature

PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT	
t_{on}	Turn-on time	$I_C = 10 \text{ A}$	$I_{B(on)} = 40 \text{ mA}$	$I_{B(off)} = -40 \text{ mA}$		0.9		μs
t_{off}	Turn-off time	$V_{BE(off)} = -4.2 \text{ V}$	$R_L = 3 \Omega$	$t_p = 20 \mu\text{s}, dc \leq 2\%$		7		μs

† Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PRODUCT INFORMATION

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TYPICAL CHARACTERISTICS

Figure 1.

Figure 2.

Figure 3.
PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS

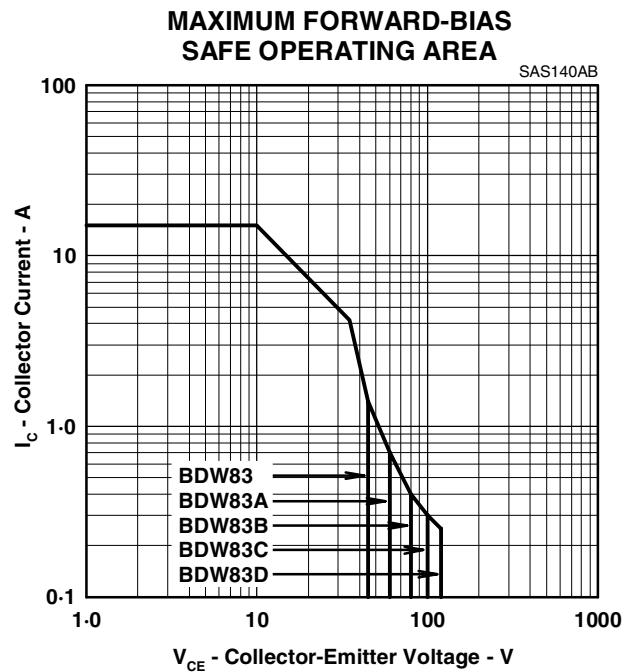


Figure 4.

THERMAL INFORMATION

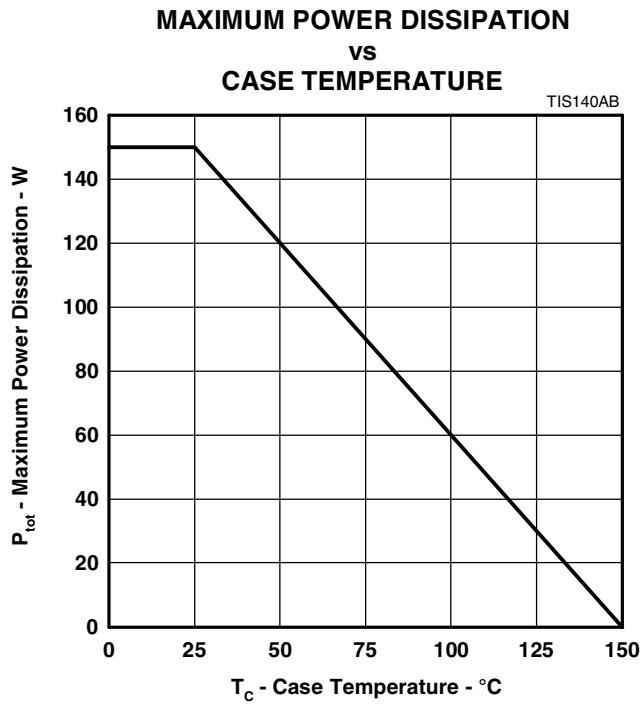


Figure 5.

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